(98S0797P1C)

As a below named inventor, I declare that my residence, mailing address and citizenship are as stated below above my name; I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD OF FORMING SEMICONDUCTOR WIRING STRUCTURES

The specification of which (check applicable box(es))

[X] was filed November 5, 1998 under PCT International Application No. PCT/JP98/04983, and amended on April 8, 1999 and August 19, 1999 both under PCT Article 34, the said PCT application having been entered in the U.S. on May 5, 2000 as United States Application No. 09/530,588, and

[X] was Amended on March 5, 2001, September 24, 2001, March 26, 2002, and April 29,

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above. I acknowledge the duty to disclose information which is material to patentability as defined in

I hereby claim foreign priority benefits under 35 U.S.C. 119(a)-(d) or 365(b) of any foreign application(s) for patent or inventor's certificate, or 35 U.S.C. 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed:

Japanese Patent Application No.9-319059, filed November 5, 1997 (Priority claimed) Japanese Patent Application No.10-207198, filed July 7, 1998 (Priority claimed)

I hereby appoint as my attorneys, with full power of substitution and revocation, to prosecute this application and transact all business in the Patent and Trademark Office connected therewith: the registrants of Oblon, Spivak, McClelland, Maier & Neustadt, P.C., 1940 Duke Street, Alexandria, Virginia 22314, Customer No. 22850, or any one of them. Send correspondence to Oblon, Spivak, McClelland, Maier & Neustadt, P.C., 1940 Duke Street, Alexandria, Virginia 22314.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

SUPPLEMENTAL DECLARATION FOR PATENT APPLICATION

(98S0797P1C)

Residence Address: Inagi-shi, Japan

Mailing Address: c/o Intellectual Property Dept., TOKYO ELECTRON LIMITED, 3-6, Akasaka

5-chome, Minato-ku, Tokyo 107-8481 Japan

Country of Citizenship: Japan

Limihiro matsuse	Sept. 30, 2003	
Kimihiro Matsuse	Date	

[2nd Inventor]

Residence Address: Nakakoma-gun, Japan

Mailing Address: c/o Intellectual Property Dept., TOKYO ELECTRON LIMITED, 3-6, Akasaka

5-chome, Minato-ku, Tokyo 107-8481 Japan

Country of Citizenship: Japan

Zayashi Otsuki	Oct. 3, 2003
Hayashi Otsuki	Date